

TOSHIBA BI-DIRECTIONAL TRIODE THYRISTOR SILICON PLANAR TYPE

SM2GZ47, SM2GZ47A, SM2JZ47, SM2JZ47A

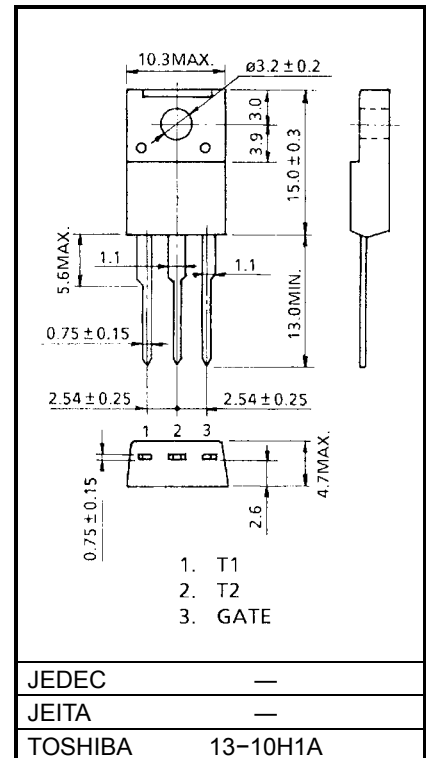
AC POWER CONTROL APPLICATIONS

- I_T (RMS) = 1A ($T_a = 65^\circ\text{C}$ without radiator)
- Gate Trigger Current : $I_{GT} = 5\text{mA Max. (TYPE "A")}$
- Repetitive Peak Off-State Voltage : $V_{DRM} = 400\text{V, } 600\text{V}$
- R.M.S On-State Current : I_T (RMS) = 2A ($T_c = 110^\circ\text{C}$)
- Isolation Voltage : $V_{ISOL} = 1500\text{V (AC, } t = 60\text{s)}$

MAXIMUM RATINGS

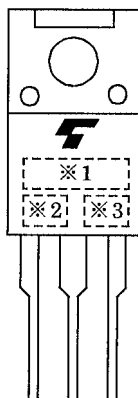
| CHARACTERISTIC | SYMBOL | RATING | UNIT |
|---|---------------------------|------------|----------------------|
| Repetitive Peak Off-State Voltage and Repetitive Peak Reverse Voltage | SM2GZ47 SM2GZ47A | 400 | V |
| | SM2JZ47 SM2JZ47A | 600 | |
| R.M.S On-State Current (Full Sine Waveform) | $T_c = 110^\circ\text{C}$ | 2 | A |
| | $T_a = 65^\circ\text{C}$ | 1 | |
| Peak One Cycle Surge On-State Current (Non-Repetitive) | I_{TSM} | 8 (50Hz) | A |
| | | 8.8 (60Hz) | |
| I^2t Limit Value | I^2t | 0.32 | A^2s |
| Peak Gate Power Dissipation | P_{GM} | 3 | W |
| Average Gate Power Dissipation | P_G (AV) | 0.3 | W |
| Peak Gate Voltage | V_{FGM} | 10 | V |
| Peak Gate Current | I_{GM} | 1.6 | A |
| Junction Temperature | T_j | -40~125 | $^\circ\text{C}$ |
| Storage Temperature Range | T_{stg} | -40~125 | $^\circ\text{C}$ |
| Isolation Voltage (AC, $t = 1\text{min.}$) | V_{ISOL} | 1500 | V |

Unit: mm



Weight: 1.7g (Typ.)

MARKING

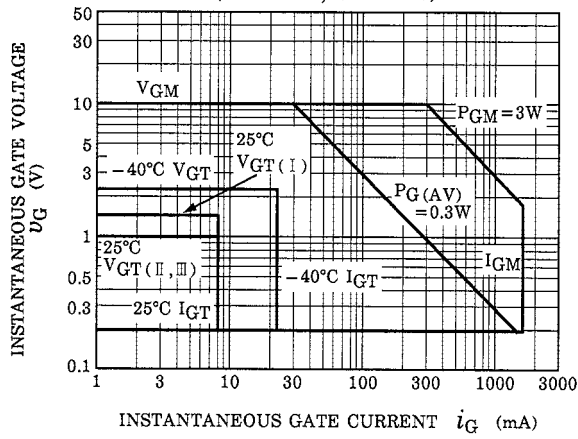


| NUMBER | SYMBOL | MARK |
|--------|---|--|
| *1 | TYPE | SM2GZ47, SM2GZ47A |
| | | SM2JZ47, SM2JZ47A |
| | | SM2GZ47A, SM2JZ47A |
| *2 | Lot Number | A |
| *3 | Lot Number Month (Starting from Alphabet A) Year (Last Decimal Digit of the Current Year) | Example 8A : January 1998 8B : February 1998 8L : December 1998 |

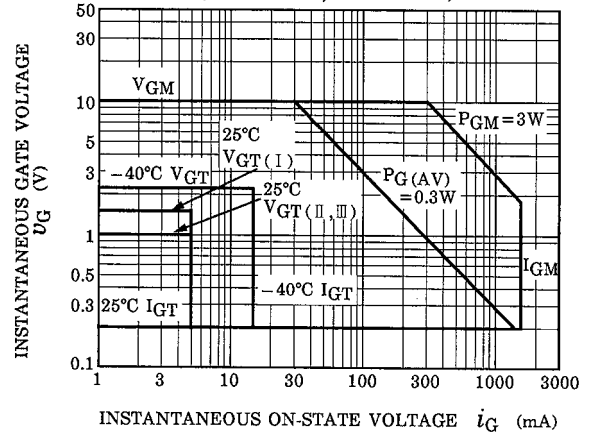
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

| CHARACTERISTIC | | SYMBOL | TEST CONDITION | MIN | TYP. | MAX | UNIT | | |
|-----------------------------------|----------------------|---------------|---|------------------|------------------|-----|-----------------------------|----|---|
| Repetitive Peak Off-State Current | | I_{DRM} | $V_{DRM} = \text{Rated}$ | — | — | 20 | μA | | |
| Gate Trigger Voltage | I | V_{GT} | $V_D = 12\text{V}$ $R_L = 20\Omega$ | T2 (+), Gate (+) | — | — | 1.5 | V | |
| | II | | | T2 (+), Gate (-) | — | — | 1 | | |
| | III | | | T2 (-), Gate (-) | — | — | 1 | | |
| | IV | | | T2 (-), Gate (+) | — | — | — | | |
| Gate Trigger Current | SM2GZ47 SM2JZ47 | I_{GT} | $V_D = 12\text{V}$ $R_L = 20\Omega$ | T2 (+), Gate (+) | — | — | 8 | mA | |
| | | | | II | T2 (+), Gate (-) | — | — | | 8 |
| | | | | III | T2 (-), Gate (-) | — | — | | 8 |
| | | | | IV | T2 (-), Gate (+) | — | — | | — |
| | SM2GZ47A SM2JZ47A | | | I | T2 (+), Gate (+) | — | — | | 5 |
| | | | | II | T2 (+), Gate (-) | — | — | | 5 |
| | | | | III | T2 (-), Gate (-) | — | — | | 5 |
| | | | | IV | T2 (-), Gate (+) | — | — | | — |
| Peak On-State Voltage | | V_{TM} | $I_{TM} = 3\text{A}$ | — | — | 1.7 | V | | |
| Gate Non-Trigger Voltage | | V_{GD} | $V_D = \text{Rated}, T_c = 125^\circ\text{C}$ | 0.2 | — | — | V | | |
| Holding Current | | I_H | $R_L = 100\Omega$ | — | — | 10 | mA | | |
| Thermal Resistance | | $R_{th(j-a)}$ | Junction to Ambient, AC | — | — | 55 | $^\circ\text{C} / \text{W}$ | | |

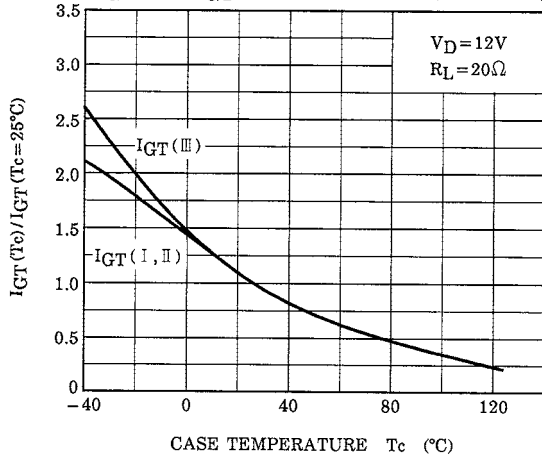
GATE TRIGGER CHARACTERISTIC
(SM2GZ47, SM2JZ47)



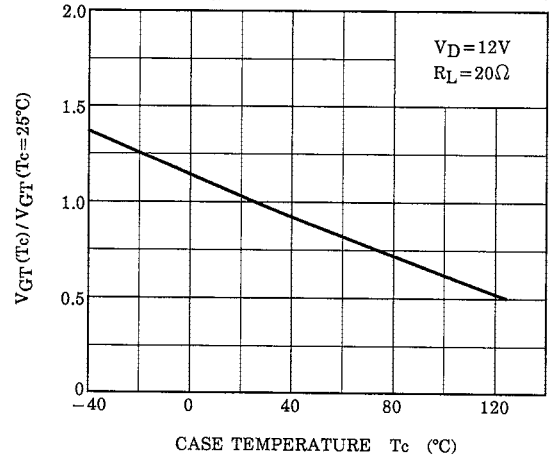
GATE TRIGGER CHARACTERISTIC
(SM2GZ47A, SM2JZ47A)



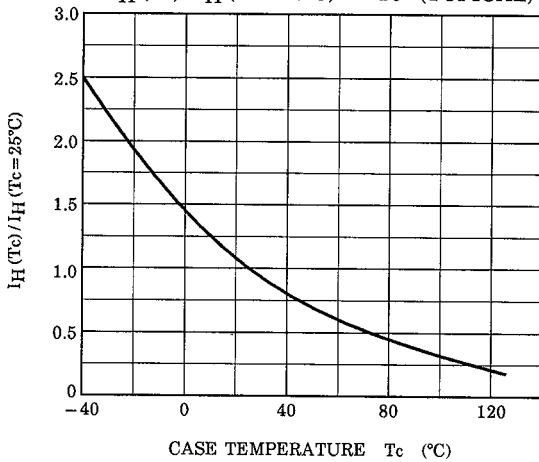
$I_{GT}(T_c) / I_{GT}(T_c = 25^\circ\text{C}) - T_c$ (TYPICAL)



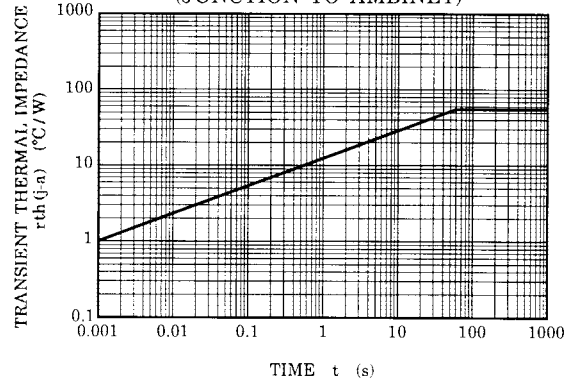
$V_{GT}(T_c) / V_{GT}(T_c = 25^\circ\text{C}) - T_c$ (TYPICAL)

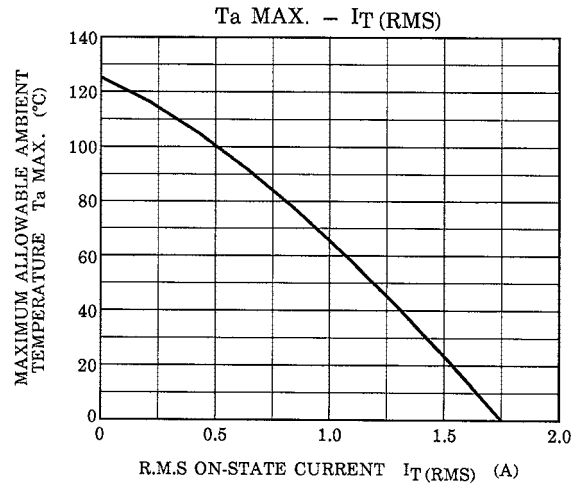
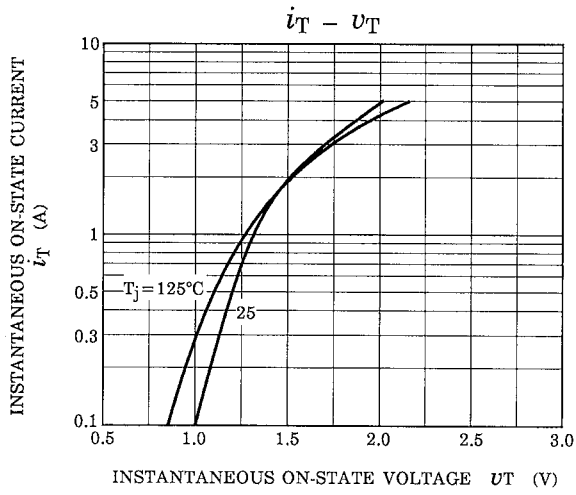


$I_H(T_c) / I_H(T_c = 25^\circ\text{C}) - T_c$ (TYPICAL)



TRANSIENT THERMAL IMPEDANCE
(JUNCTION TO AMBIENT)





<CONDITION>

- ◆ NO HEAT SINK
- ◆ LEAD FORMING : LB182
- ◆ PRINT BOARD

($t = 1.6\text{mm}$
SOLDER LAND : $2\text{mm}\phi$)

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